

<b>Notice of References Cited</b>	Application/Control No. 10/659,435	Applicant(s)/Patent Under Reexamination BASCERI ET AL.	
	Examiner Evan Pert	Art Unit 2826	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,046,084 A	04-2000	Wei et al.	438/255
	C	US-6,027,970 A	02-2000	Sharan et al.	438/255
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	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	M. Gutsche et al., "Capacitance Enhancement Techniques for Sub-100nm Trench DRAMs", International Electron Devices meeting, 2001. December 2001, pages 18.6.1 to 18.6.4.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.